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November 2013

# FQD19N10L

# N-Channel QFET $^{\rm @}$ MOSFET 100 V, 15.6 A, 100 m $\Omega$

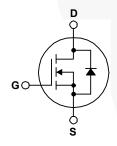
# **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 15.6 A, 100 V,  $R_{DS(on)}$  = 100 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V
- Low Gate Charge (Typ. 14 nC)
- · Low Crss (Typ. 35 pF)
- 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQD19N10LTM	Unit	
$V_{DSS}$	Drain-Source Voltage		100	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		C)	15.6	Α
		- Continuous (T <sub>C</sub> = 100	)°C)	9.8	Α
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	62.4	Α
V <sub>GSS</sub>	Gate-Source Vo	oltage		± 20	V
E <sub>AS</sub>	Single Pulsed A	ingle Pulsed Avalanche Energy (Note 2)		220	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	15.6	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *			2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C) - Derate Above 25°C			50	W
				0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

## **Thermal Characteristics**

Symbol	Parameter	FQD19N10LTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD19N10LTM	FQD19N10L	D-PAK	Tape and Reel	330 mm	16 mm	2500 units

# Electrical Characteristics T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$				V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.09		V/°C
I <sub>DSS</sub>	Zara Oata Vallana Dasia Ourrant	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 80 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.0		2.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.8 A V <sub>GS</sub> = 5 V, I <sub>D</sub> = 7.8 A		0.074 0.082	0.10 0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 7.8 A	\	14		S
	ic Characteristics			670	870	- n-
Ciss	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		670		pF
C <sub>oss</sub>	Output Capacitance Reverse Transfer Capacitance	f = 1.0 MHz		160 35	210 45	pF
Orss	Reverse Transfer Capacitance			33	45	pF
Switchi	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 19 A,		14	38	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		410	830	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1.0 - 1 - 1		20	50	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		140	290	ns
$Q_g$	Total Gate Charge	V <sub>DS</sub> = 80 V, I <sub>D</sub> = 19 A,		14	18	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 5 V		2.9		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		9.2		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				15.6	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				62.4	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 15.6 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 19 A,		80	//	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		0.195	//	μС

- Notes: 
  1. Repetitive rating: pulse-width limited by maximum junction temperature. 
  2. L = 1.35 mH,  $I_{AS}$  = 15.6 A,  $V_{DD}$  = 25 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 
  3.  $I_{SD}$  ≤ 19 A, di/dt ≤ 300 A/µs,  $V_{DD}$  ≤ BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 
  4. Essentially independent of operating temperature.

# **Typical Characteristics**

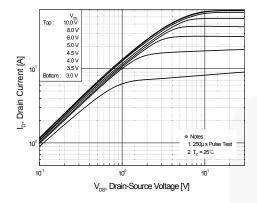


Figure 1. On-Region Characteristics

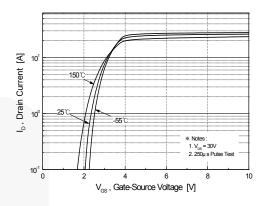


Figure 2. Transfer Characteristics

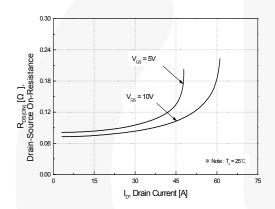


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

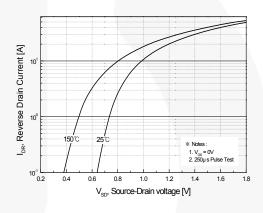


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

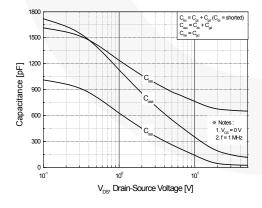


Figure 5. Capacitance Characteristics

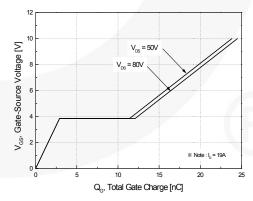


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

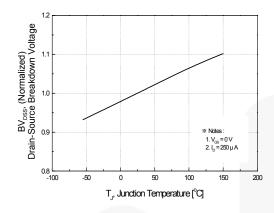
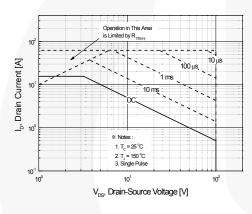


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



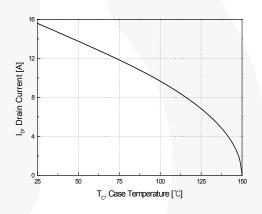


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

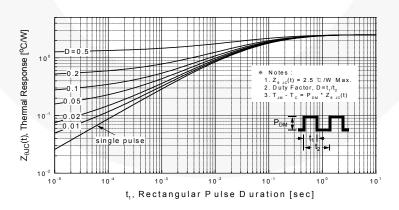


Figure 11. Transient Thermal Response Curve

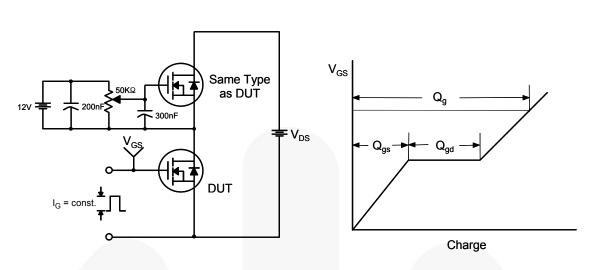


Figure 12. Gate Charge Test Circuit & Waveform

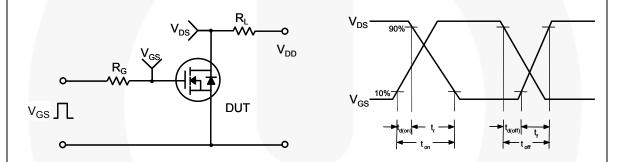


Figure 13. Resistive Switching Test Circuit & Waveforms

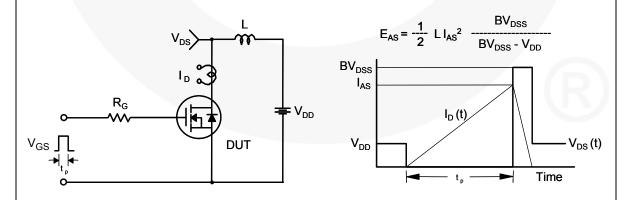
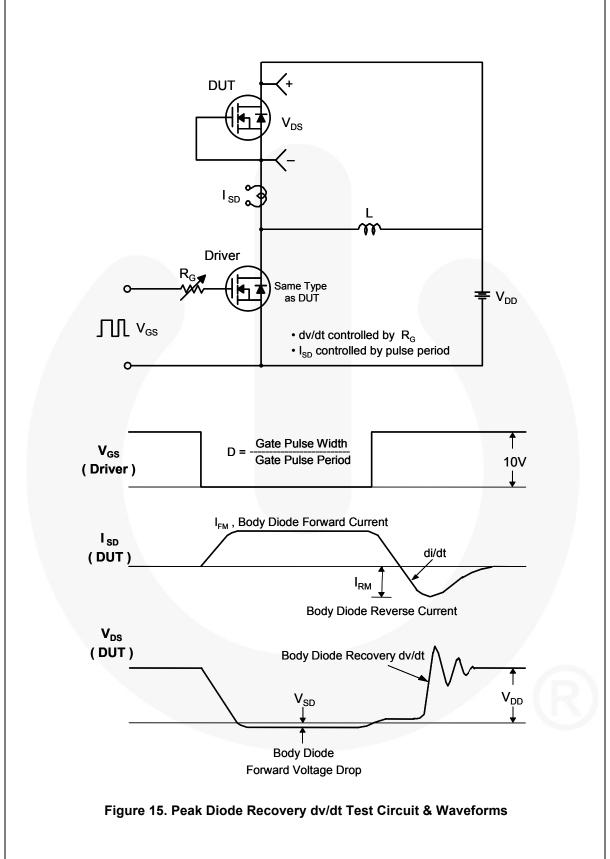


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**

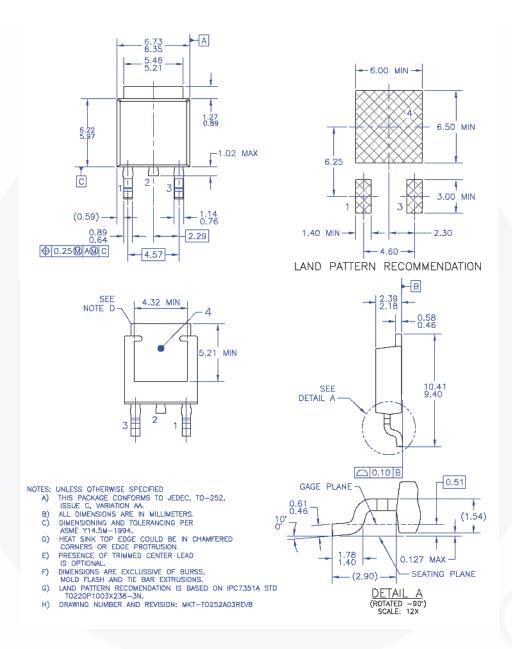


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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